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# DMG4413LSS-13

Diodes Incorporated

MOSFET MOSFET,P-CHANNEL

Any questions,please feel free to contact us.  
[info@kaimte.com](mailto:info@kaimte.com)

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
-30V	7.5mΩ @ V <sub>GS</sub> = -10V	-12A
	10.2mΩ @ V <sub>GS</sub> = -4.5V	-10A

## Description

This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## Applications

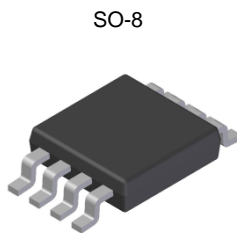
- Backlighting
- Power Management Functions
- DC-DC Converters

## Features and Benefits

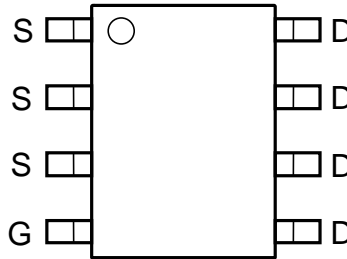
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([DMG4413LSSQ](#))**

## Mechanical Data

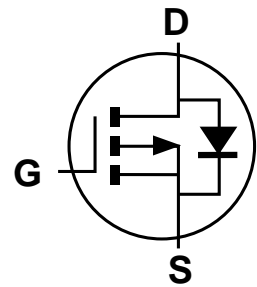
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram Below
- Terminals: Finish — Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.074 grams (Approximate)



Top View



Top View  
Pin-out



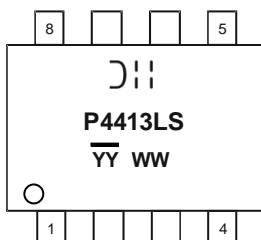
Equivalent Circuit

## Ordering Information (Note 4)

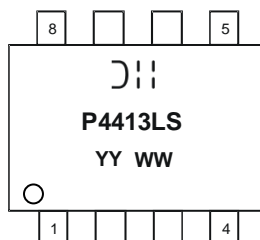
Part Number	Case	Packaging
DMG4413LSS-13	SO-8	2500/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



Chengdu A/T Site



Shanghai A/T Site

⌋⌋⌋ = Manufacturer's Marking  
 P4413LS = Product Type Marking Code  
 YYWW = Date Code Marking  
 YY or Y Y = Year (ex: 18 = 2018)  
 WW = Week (01 to 53)  
 YY = Date Code Marking for SAT (Shanghai Assembly/ Test Site)  
 Y Y = Date Code Marking for CAT (Chengdu Assembly/ Test Site)

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V <sub>DSS</sub>	-30	V
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = -10V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-12 -10	A
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-22 -17	A
Continuous Drain Current (Note 6) V <sub>GS</sub> = -4.5V	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-10 -8	A
	t < 10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	-18 -14	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	-45	A
Maximum Body Diode Continuous Current			I <sub>S</sub>	-4	A

**Thermal Characteristics**

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	P <sub>D</sub>	1.7	W
	T <sub>A</sub> = +70°C		1.1	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R <sub>θJA</sub>	74	°C/W
	t < 10s		22	
Total Power Dissipation (Note 6)	T <sub>A</sub> = +25°C	P <sub>D</sub>	2.2	W
	T <sub>A</sub> = +70°C		1.4	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R <sub>θJA</sub>	56	°C/W
	t < 10s		17	
Thermal Resistance, Junction to Case (Note 6)	Steady State	R <sub>θJC</sub>	2.5	
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-30	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250µA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	-1	µA	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±1	µA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-1.1	-1.6	-2.1	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250µA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	6.3	7.5	mΩ	V <sub>GS</sub> = -10V, I <sub>D</sub> = -13A V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -10A
		—	7.9	10.2		
Forward Transconductance	g <sub>fs</sub>	—	26	—	S	V <sub>DS</sub> = -15V, I <sub>D</sub> = -13A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2.7A
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	C <sub>iss</sub>	—	4965	—	pF	V <sub>DS</sub> = -15V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	1487	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	711	—	pF	
Gate Resistance	R <sub>G</sub>	—	7.3	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V f = 1.0MHz
<b>SWITCHING CHARACTERISTICS (Note 8)</b>						
Total Gate Charge	Q <sub>G</sub>	—	46	—	nC	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -5V I <sub>D</sub> = -13A
Gate-Source Charge	Q <sub>GS</sub>	—	17	—		
Gate-Drain Charge	Q <sub>GD</sub>	—	16	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	15	—	ns	V <sub>DS</sub> = -15V, V <sub>GS</sub> = -10V, I <sub>D</sub> = -1A, R <sub>G</sub> = 6.0Ω
Rise Time	t <sub>R</sub>	—	9	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	160	—		
Fall Time	t <sub>F</sub>	—	66	—		

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
  7. Short duration pulse test used to minimize self-heating effect.
  8. Guaranteed by design. Not subject to product testing.

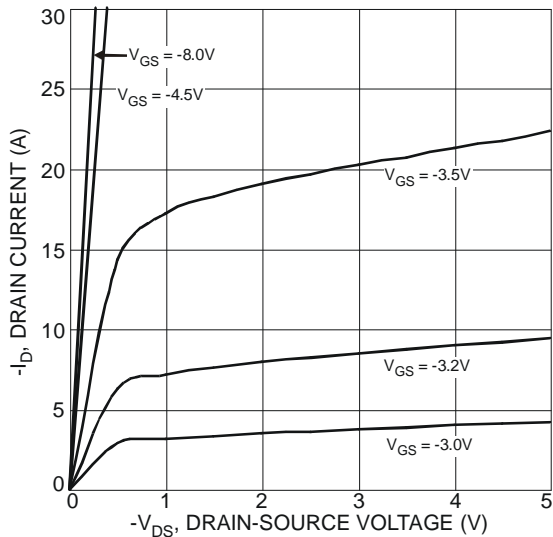


Fig. 1 Typical Output Characteristic

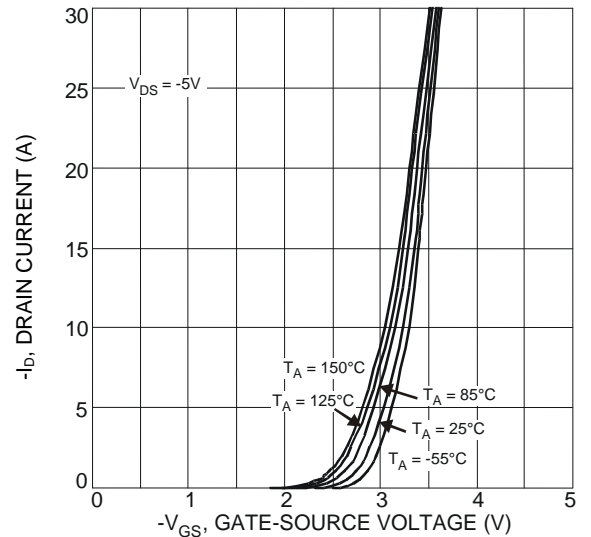


Fig. 2 Typical Transfer Characteristic

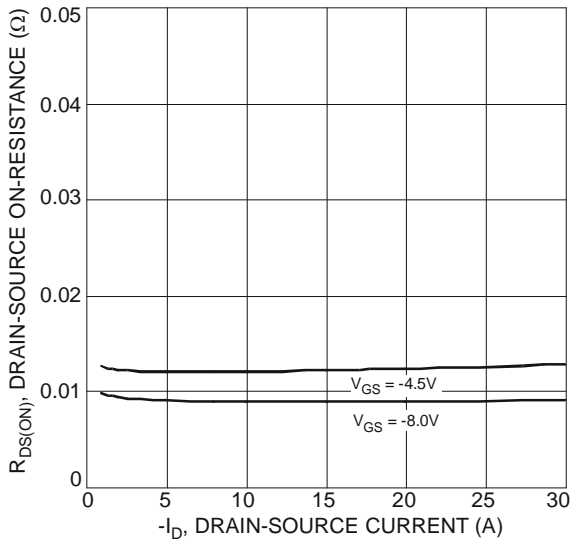


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

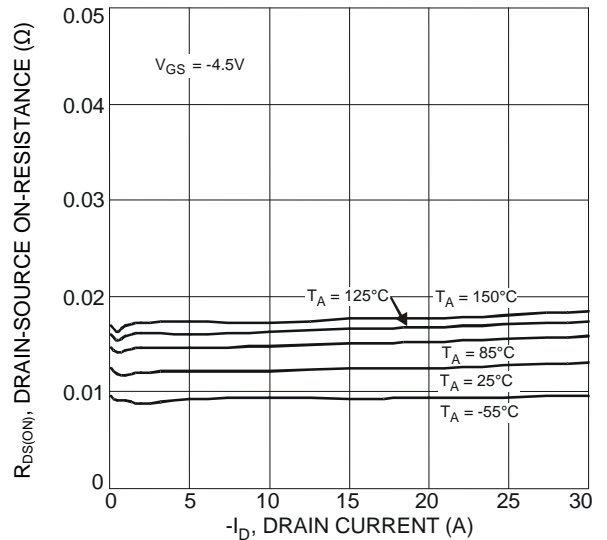


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

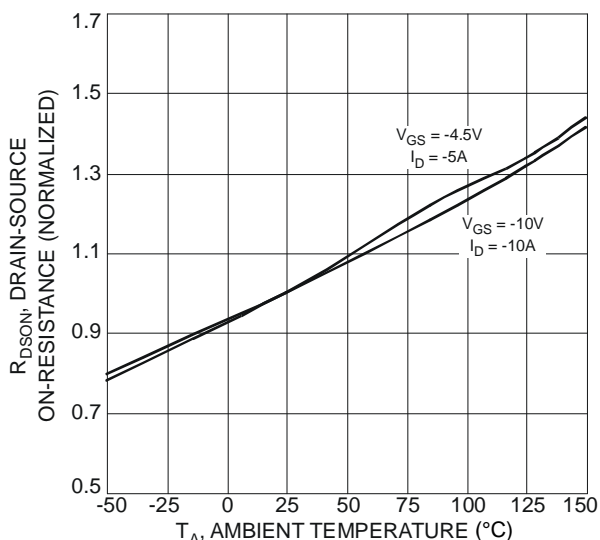


Fig. 5 On-Resistance Variation with Temperature

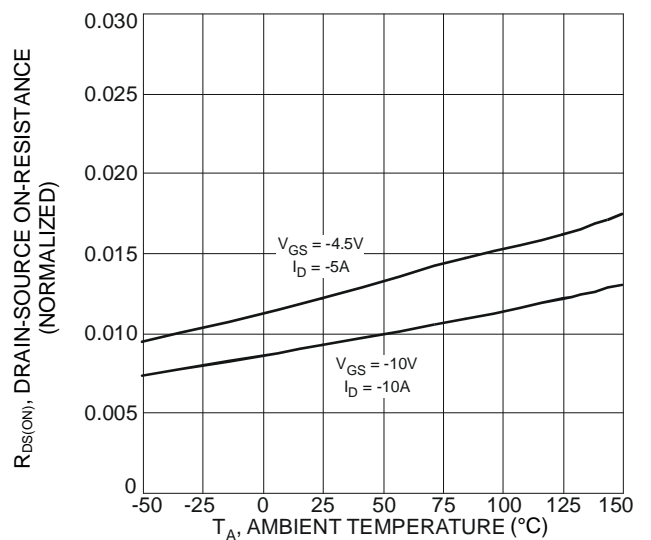


Fig. 6 On-Resistance Variation with Temperature

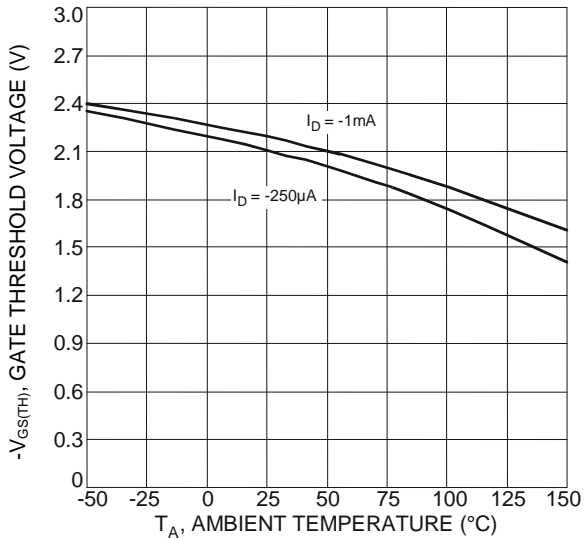


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

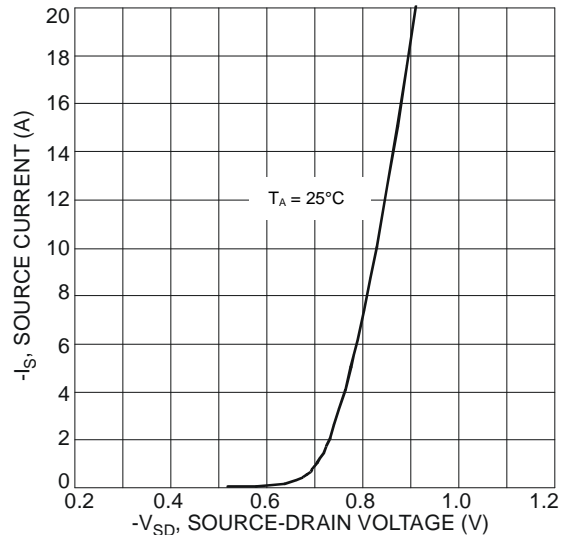


Fig. 8 Diode Forward Voltage vs. Current

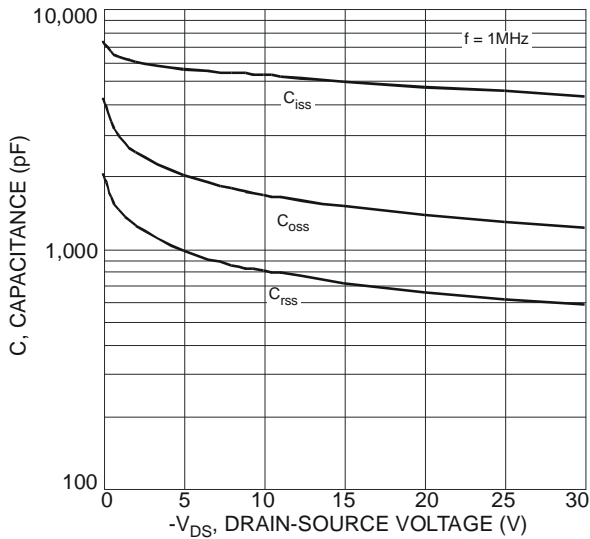


Fig. 9 Typical Total Capacitance

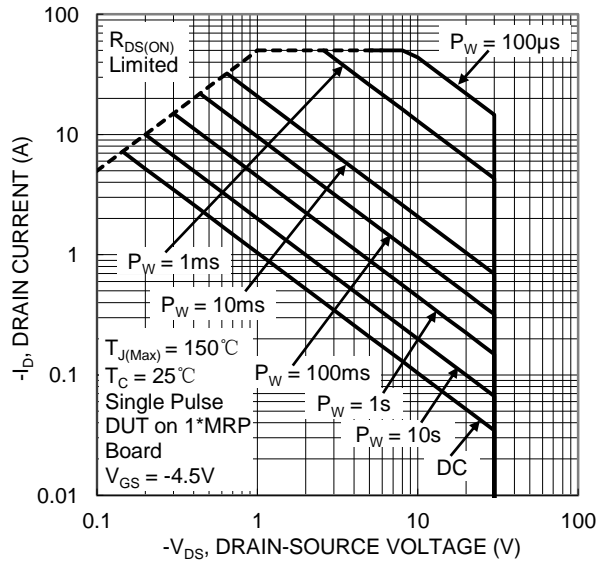
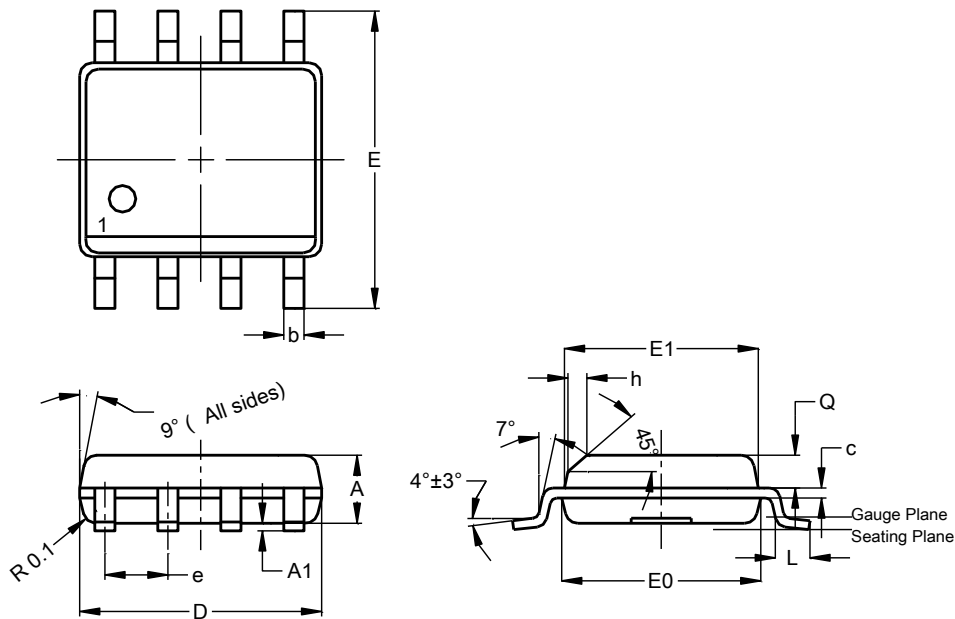


Fig. 10 SOA, Safe Operation Area

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8**

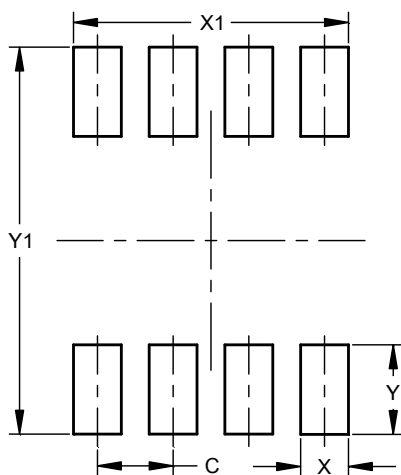


SO-8			
Dim	Min	Max	Typ
A	1.40	1.50	1.45
A1	0.10	0.20	0.15
b	0.30	0.50	0.40
c	0.15	0.25	0.20
D	4.85	4.95	4.90
E	5.90	6.10	6.00
E1	3.80	3.90	3.85
E0	3.85	3.95	3.90
e	--	--	1.27
h	-	--	0.35
L	0.62	0.82	0.72
Q	0.60	0.70	0.65
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SO-8**



Dimensions	Value (in mm)
C	1.27
X	0.802
X1	4.612
Y	1.505
Y1	6.50

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